Title (en)

GAS-PHASE DEPOSITION PROCESS

Title (de)

GASPHASENABSCHEIDUNGSVERFAHREN

Title (fr)

PROCÉDÉ DE DÉPÔT EN PHASE GAZEUSE

Publication

EP 3119921 A1 20170125 (FR)

Application

EP 15711152 A 20150319

Priority

- FR 1452385 A 20140321
- EP 2015055821 W 20150319

Abstract (en)

[origin: WO2015140261A1] The invention relates to a layer-deposition process, which includes: injecting a first reagent in gaseous phase into the deposition chamber (30) via a first injection path (40), and injecting a second gas-phase reagent into the deposition chamber (30) via a second injection path (50), the second injection path (50) being separate from the first injection path (40). The pressure in the deposition chamber (30) is greater than a predetermined value for the entire duration of the process. Said process is characterized in that the first reagent is fed into the deposition chamber (30) according to a first pulse sequence, and the second reagent is fed into the chamber according to a second pulse sequence. The first pulse sequence and the second pulse sequence are out of phase with one another.

IPC 8 full level

C23C 16/455 (2006.01)

CPC (source: CN EP KR US)

C23C 16/45523 (2013.01 - CN EP KR US); **C23C 16/45525** (2013.01 - US); **C23C 16/45574** (2013.01 - CN EP KR US)

Citation (search report)

See references of WO 2015140261A1

Citation (examination)

- US 2004235191 A1 20041125 - HASEGAWA TOSHIO [JP]
- JP 2010084156 A 20100415 - TOKYO ELECTRON LTD
- JP 2006009152 A 20060112 - TOKYO ELECTRON LTD
- US 2003108674 A1 20030612 - CHUNG HUA [US], et al

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

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DOCDB simple family (publication)

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EP 2015055821 W 20150319; CN 201580015091 A 20150319; EP 15711152 A 20150319; FR 1452385 A 20140321; JP 2017500419 A 20150319; KR 20167027417 A 20150319; SG 11201607862T A 20150319; US 201515127218 A 20150319